

## Description

The PMV48XP uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

### **General Features**

$$\begin{split} V_{DS} &= -20V, I_{D} = -4.2A \\ R_{DS(ON)} < 55m\Omega@~V_{GS} \mbox{=} -4.5V \\ R_{DS(ON)} < 75m~\Omega@~V_{GS} \mbox{=} -2.5V \end{split}$$

## Application

PWM applications Load switch Power management

#### Package Marking and Ordering Information

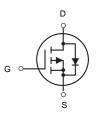
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|------------|----------|------------|----------|
| Product ID | Pack     | Brand      | Qty(PCS) |
| PMV48XP    | SOT-23   | HXY MOSFET | 3000     |

#### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| Symbol  | Parameter  | Limit      | Unit |
|---------|--|------------|------|
| VDS     | Drain-Source Voltage                             | -20        | V    |
| Vgs     | Gate-Source Voltage                              | ±12        | V    |
| ID      | Drain Current-Continuous                         | -4.2       | A    |
| Ідм     | Drain Current-Pulsed (Note 1)                    | -15        | A    |
| PD      | Maximum Power Dissipation                        | 1.7        | W    |
| Тј,Тѕтс | Operating Junction and Storage Temperature Range | -55 To 150 | °C   |
| Reja    | Thermal Resistance, Junction-to-Ambient (Note 2) | 74         | °C/W |







P-Channel MOSFET



## Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>Cunless otherwise noted)

| Parameter                          | Symbol              | Condition   | Min     | Тур  | Max  | Unit |  |
|------------------------------------|---------------------|---|---------|------|------|------|--|
| Off Characteristics                | ·                   |   |         |      |      |      |  |
| Drain-Source Breakdown Voltage     | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =-250µA                        | -20     | -    | -    | V    |  |
| Zero Gate Voltage Drain Current    | I <sub>DSS</sub>    | V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V                         | -       | -    | -1   | μA   |  |
| Gate-Body Leakage Current          | I <sub>GSS</sub>    | V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V                         | -       | -    | ±100 | nA   |  |
| On Characteristics (Note 3)        |                     |   |         |      |      |      |  |
| Gate Threshold Voltage             | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA          | -0.45   | -0.7 | -1.0 | V    |  |
|                                    | 5                   | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A                       | - 48 55 |      | 55   |      |  |
| Drain-Source On-State Resistance   | R <sub>DS(ON)</sub> | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A                       | -       | 60   | 75   | -mΩ  |  |
| Forward Transconductance           | <b>g</b> fs         | V <sub>DS</sub> =-5V,I <sub>D</sub> =-4.2A                        | -       | 6    | -    | S    |  |
| Dynamic Characteristics (Note4)    |                     |   | u       |      |      |      |  |
| Input Capacitance                  | C <sub>lss</sub>    |   | -       | 740  | -    | PF   |  |
| Output Capacitance                 | C <sub>oss</sub>    | - V <sub>DS</sub> =-4V,V <sub>GS</sub> =0V,<br>F=1.0MHz           | -       | 290  | -    | PF   |  |
| Reverse Transfer Capacitance       | C <sub>rss</sub>    |   | -       | 190  | -    | PF   |  |
| Switching Characteristics (Note 4) | ·                   |   |         |      |      |      |  |
| Turn-on Delay Time                 | t <sub>d(on)</sub>  |   | -       | 12   | -    | nS   |  |
| Turn-on Rise Time                  | tr                  | V <sub>DD</sub> =-4V, ,R <sub>L</sub> =-1.2Ω,                     | -       | 35   | -    | nS   |  |
| Turn-Off Delay Time                | t <sub>d(off)</sub> | $V_{GEN}$ =-4.5V,Rg=1 $\Omega$                                    | -       | 30   | -    | nS   |  |
| Turn-Off Fall Time                 | t <sub>f</sub>      |   | -       | 10   | -    | nS   |  |
| Total Gate Charge                  | Qg                  |   | -       | 7.8  | -    | nC   |  |
| Gate-Source Charge                 | Q <sub>gs</sub>     | V <sub>DS</sub> =-4V,I <sub>D</sub> =-4.1A,V <sub>GS</sub> =-4.5V | -       | 1.2  | -    | nC   |  |
| Gate-Drain Charge                  | Q <sub>gd</sub>     | 1   | -       | 1.6  | -    | nC   |  |
| Drain-Source Diode Characteristics | •                   |   |         |      |      |      |  |
| Diode Forward Voltage (Note 3)     | V <sub>SD</sub>     | V <sub>GS</sub> =0V,I <sub>S</sub> =-4.1A                         | -       | -    | -1.2 | V    |  |
| Diode Forward Current (Note 2)     | Is                  |   | -       | -    | -4.1 | Α    |  |

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**

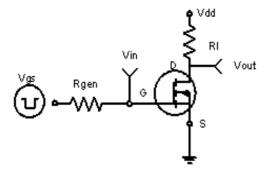
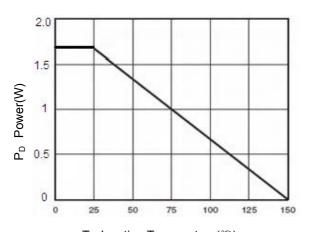
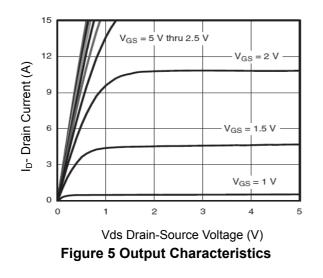


Figure 1:Switching Test Circuit



T<sub>J</sub>-Junction Temperature(℃) **Figure 3 Power Dissipation** 



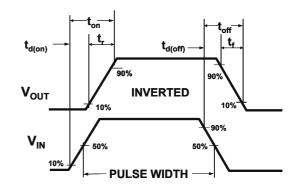
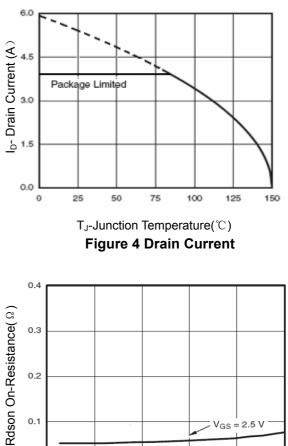


Figure 2:Switching Waveforms



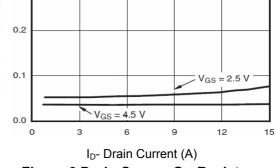
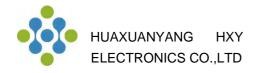
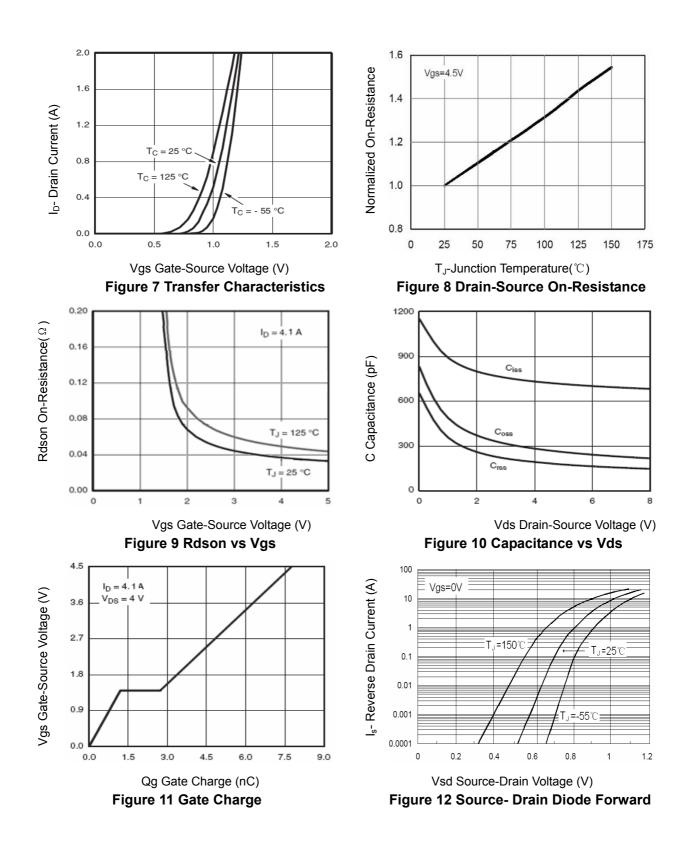


Figure 6 Drain-Source On-Resistance







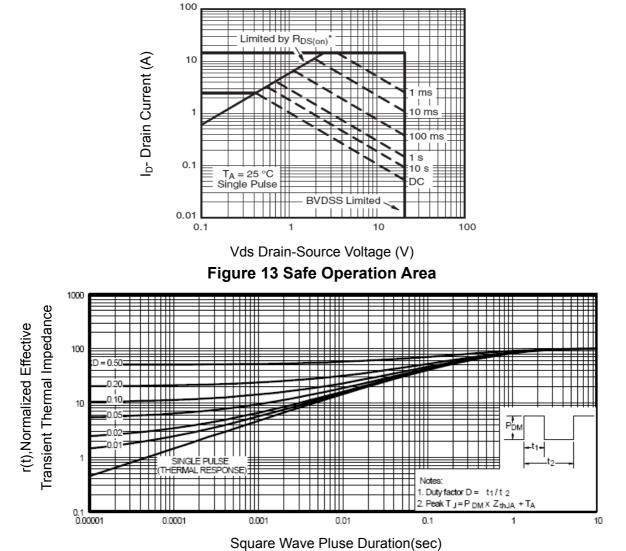
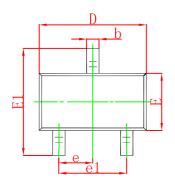
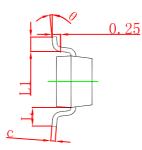


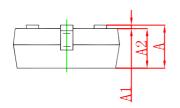
Figure 14 Normalized Maximum Transient Thermal Impedance



# **SOT-23 Package Outline Dimensions**

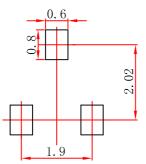






| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |  |
|--------|---------------------------|-------|----------------------|-------|--|
|        | Min                       | Max   | Min                  | Max   |  |
| А      | 0.900                     | 1.150 | 0.035                | 0.045 |  |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |  |
| A2     | 0.900                     | 1.050 | 0.035                | 0.041 |  |
| b      | 0.300                     | 0.500 | 0.012                | 0.020 |  |
| С      | 0.080                     | 0.150 | 0.003                | 0.006 |  |
| D      | 2.800                     | 3.000 | 0.110                | 0.118 |  |
| Е      | 1.200                     | 1.400 | 0.047                | 0.055 |  |
| E1     | 2.250                     | 2.550 | 0.089                | 0.100 |  |
| e      | 0.950 TYP                 |       | 0.037 TYP            |       |  |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079 |  |
| L      | 0.550 REF                 |       | 0.022 REF            |       |  |
| L1     | 0.300                     | 0.500 | 0.012                | 0.020 |  |
| θ      | 0°                        | 8°    | 0°                   | 8°    |  |

# SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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